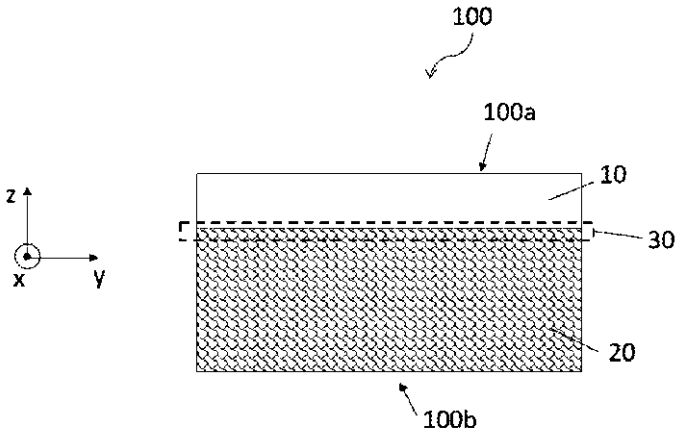
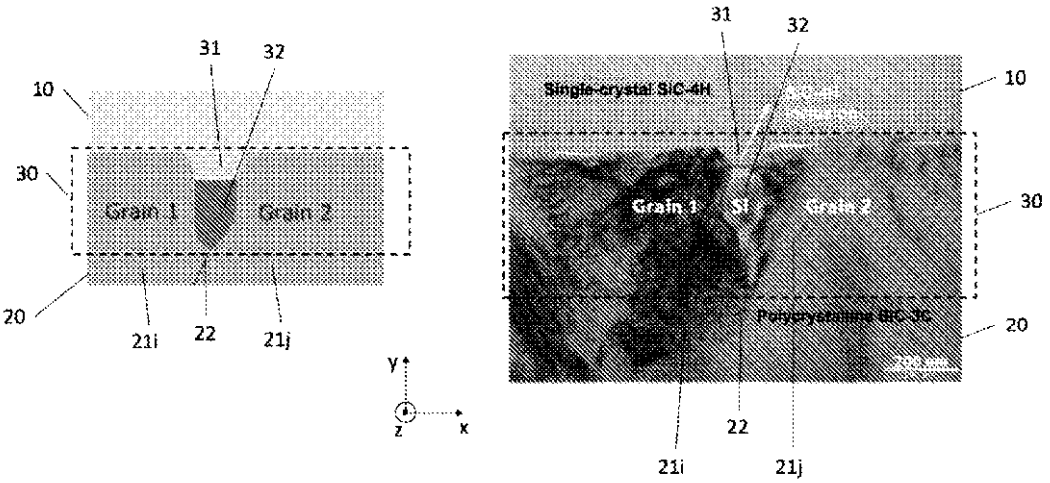
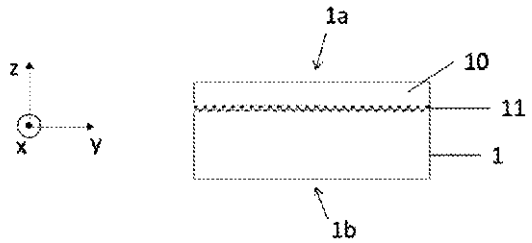
[Fig. 1]



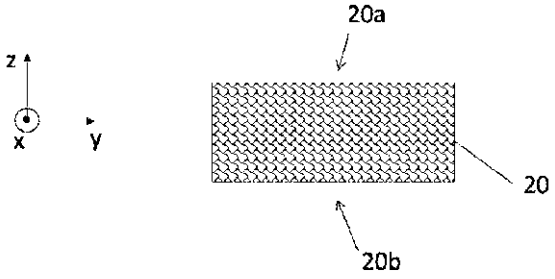
[Fig. 2]



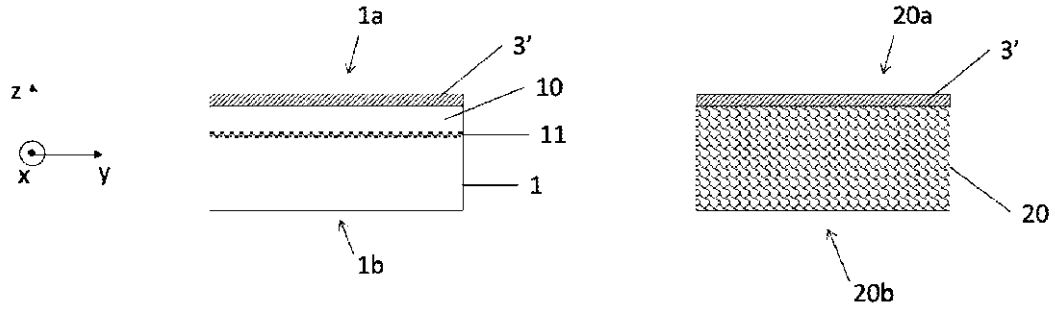
[Fig. 3a]



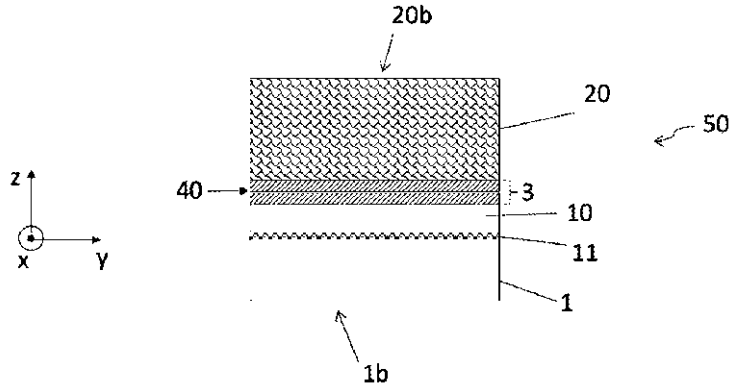
[Fig. 3b]



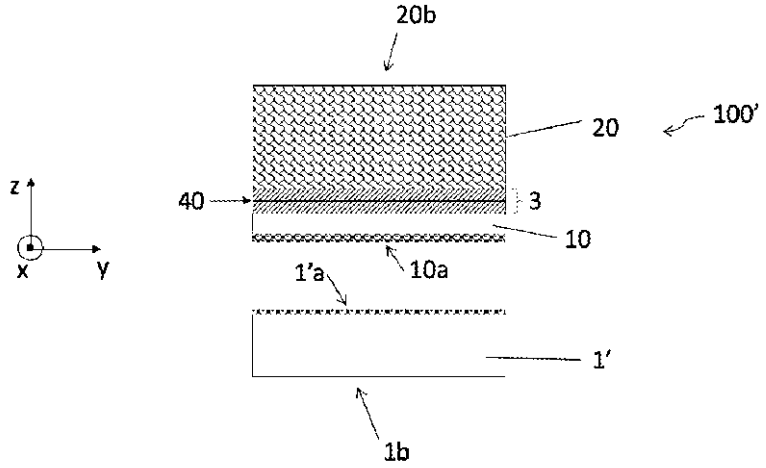
[Fig. 3c]



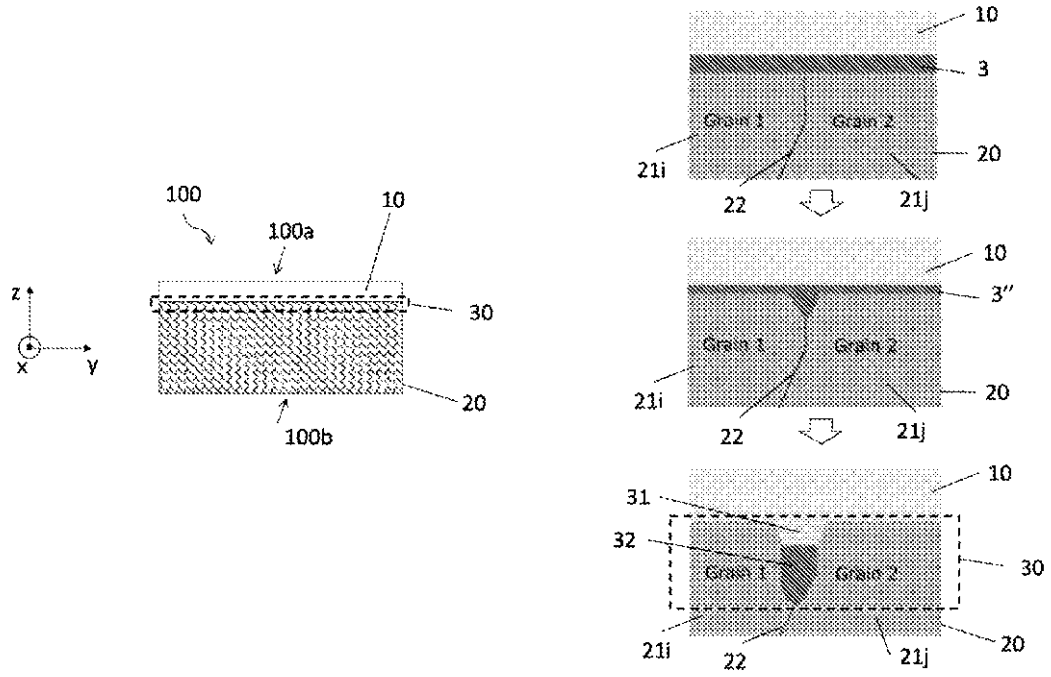
[Fig. 3d]



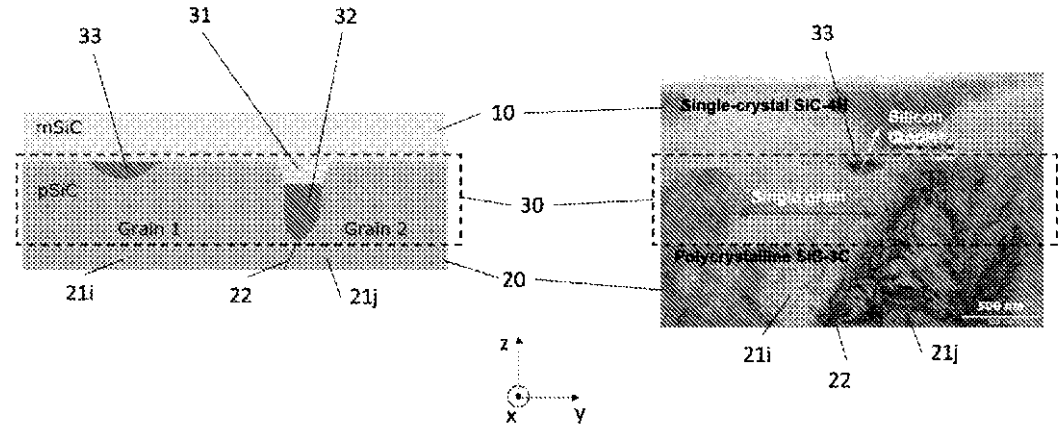
[Fig. 3e]



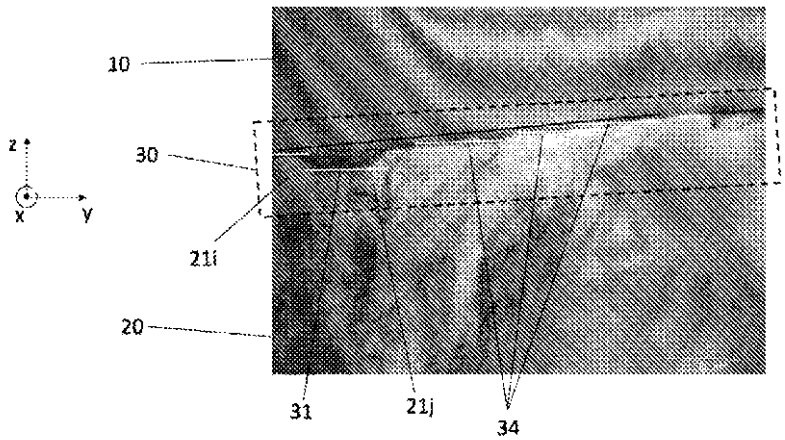
[Fig. 3f]



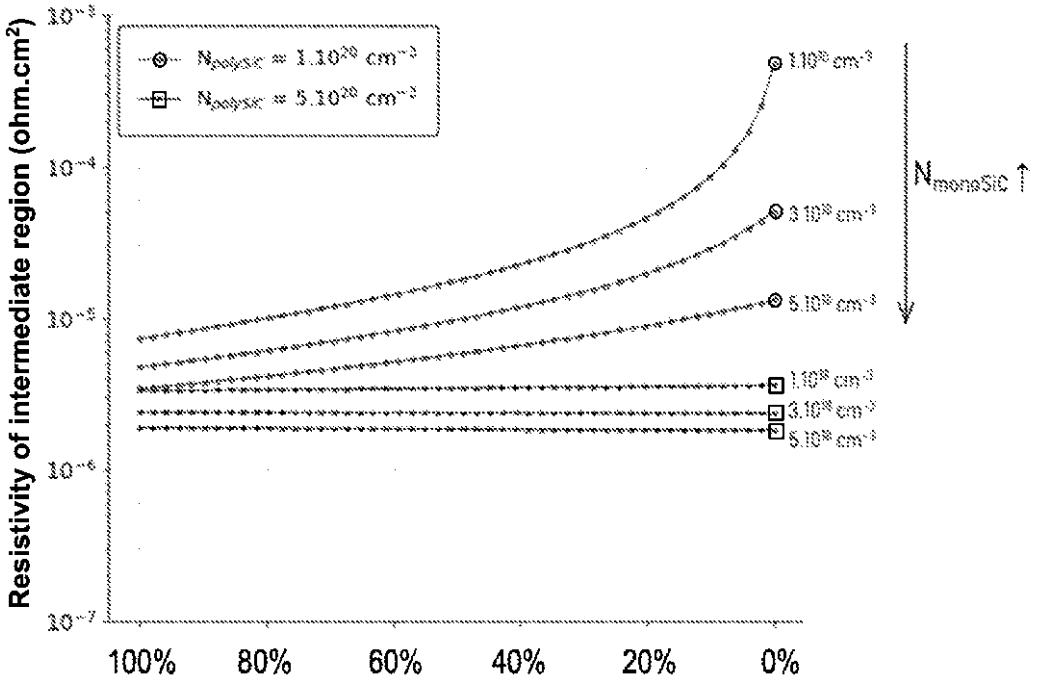
[Fig. 4]



[Fig. 5]



[Fig. 6]


Resistivity of intermediate region (ohm.cm²)
100%
80%
60%
40%
20%
0%
% of surface area of the bonded face of the carrier substrate in which the grains have a size less than or equal to 500 nm
N_monoSiC ↑